





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	2mΩ @ V _{GS} = 5V	280mA
50V	2.5mΩ @ V _{GS} = 2.5V	258mA
	3mΩ @ V _{GS} = 1.8V	235mA

Features

- Low On-Resistance
- Very Low Gate Threshold Voltage (1.0V max)
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

General Purpose Interfacing Switch

Mechanical Data

Drain

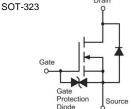
EQUIVALENT CIRCUIT

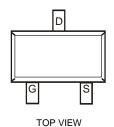
- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
 Leadframe. Solderable per MIL-STD-202, Method 208 63
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)





TOP VIEW





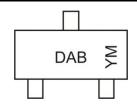
Ordering Information (Note 5)

Part Number	Case	Packaging
DMN5L06WKQ-7	SOT-323	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



DAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	201	2	2013		2014	20	15	2016		2017	2	2018
Code	Z		Α		В	()	D		Е		F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 6) Continuous Pulsed (Note 7)	I _D	300 800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	250	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

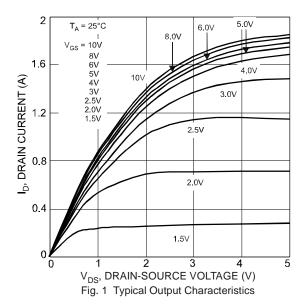
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

		T I		r _	r		
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		BV _{DSS}	50	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	$@T_C = +25^{\circ}C$	I _{DSS}		_	60	nA	$V_{DS} = 50V, V_{GS} = 0V$
					1	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$
Gate-Body Leakage		IGSS	_	_	500	nA	$V_{GS} = \pm 10V$, $V_{DS} = 0V$
					50	nA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage		V _{GS(th)}	0.49	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
			_	_	3.0		$V_{GS} = 1.8V, I_D = 50mA$
Static Drain-Source On-Resistance		R _{DS} (ON)	_	_	2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$
		, ,	_	_	2.0		$V_{GS} = 5.0V, I_D = 50mA$
On-State Drain Current		I _{D(ON)}	0.5	1.4	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		Y _{fs}	200	_	_	mS	$V_{DS} = 10V, I_{D} = 0.2A$
Source-Drain Diode Forward Voltage		V_{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance		C _{iss}	_	_	50	pF	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Output Capacitance		Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	_	5.0	pF	1 = 1.0WI12	
Turn-On Delay Time		$t_{D(on)}$	_	2.1	_	ns	
Turn-On Rise Time			_	1.8	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time			_	14.4	_	ns	$R_G = 25\Omega$, $I_D = 200mA$
Turn-Off Fall Time			_	8.4	_	ns	

Notes:

- 6. Device mounted on FR-4 PCB.
- 7. Pulse width ≤10µS, Duty Cycle ≤1%.
- 3. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.





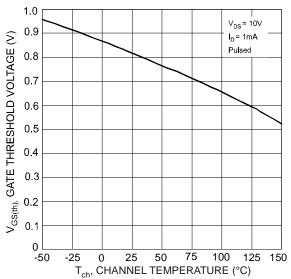


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

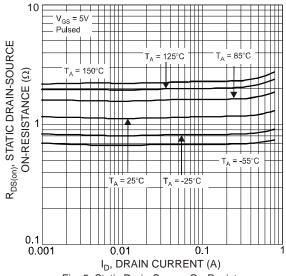
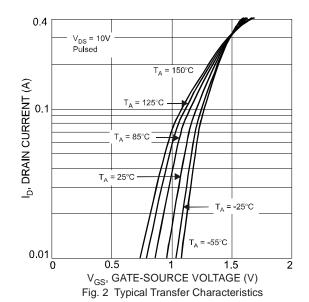


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



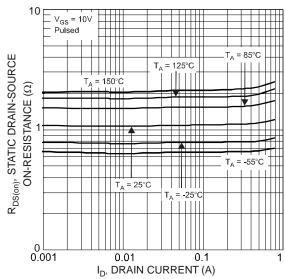
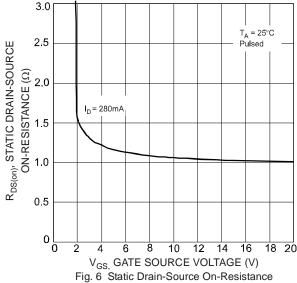


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current



vs. Gate-Source Voltage



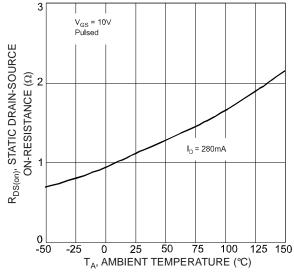


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

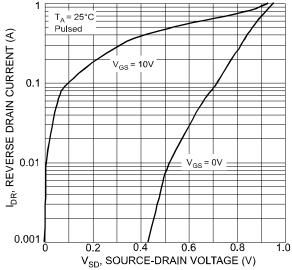
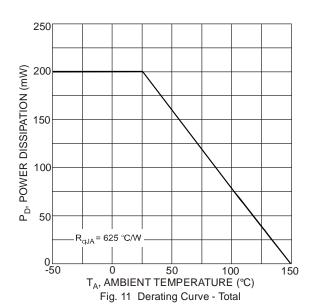


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage



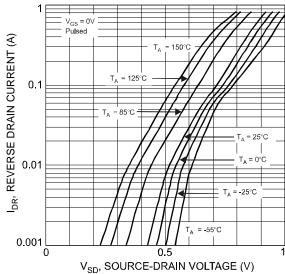


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

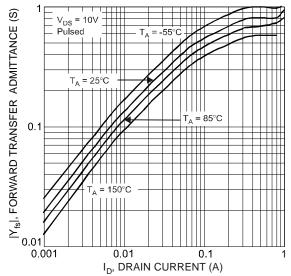
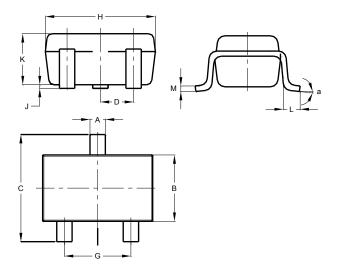


Fig.10 Forward Transfer Admittance vs. Drain Current



Package Outline Dimensions

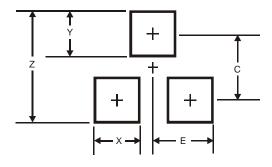
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT323							
Dim	Min	Max	Тур					
Α	0.25	0.40	0.30					
В	1.15	1.35	1.30					
С	2.00	2.20	2.10					
D	0.650 BSC							
F	0.375	0.425						
G	1.20	1.40	1.30					
Н	1.80	2.20	2.15					
J	0.00	0.10	0.05					
K	0.90	1.00	0.95					
L	0.25	0.40	0.30					
M	0.10	0.18	0.11					
а	8°C							
All [All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
F	1.0



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